

Capsule Thyristor

Line Thyristor

SKT 1203

Preliminary Data

Features

- Hermetic metal case with epoxy insulator
- Capsule package for double sided cooling
- Off-state and reverse voltages up to 1800 V
- Amplifying gate

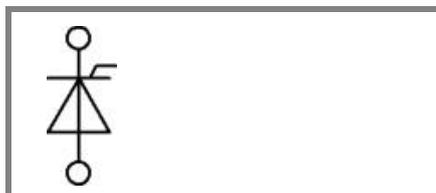
Typical Applications

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Recommended snubber network e. g. for $V_{VRMS} \leq 400$ V:
 $R = 33 \Omega / 32$ W, $C = 1 \mu F$

1) SKT 1203/08 D has $(dv/dt)_{cr} = 500$ V/ μs

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 2800$ A (maximum value for continuous operation) $I_{TAV} = 1200$ A (sin. 180; DSC; $T_c = 85$ °C)	
800	800		SKT 1203/08 D ¹⁾
1200	1200		SKT 1203/12 E
1400	1400		SKT 1203/14 E
1600	1600		SKT 1203/16 E
1800	1800		SKT 1203/18 E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 100$ (85) °C;	840 (1200)	A
I_D	2 x P8/180F; $T_a = 35$ °C; B2 / B6	1440 / 2050	A
	2 x P19/190F; $T_a = 35$ °C; B2 / B6	1550 / 2200	A
I_{RMS}	2 x P8/180F; $T_a = 35$ °C; W1C	1600	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	30000	A
	$T_{vj} = 125$ °C; 10 ms	25500	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	4500000	A ² s
	$T_{vj} = 125$ °C; 8,3 ... 10 ms	3250000	A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 3600$ A	max. 1,65	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,95	V
r_T	$T_{vj} = 125$ °C	max. 0,18	m Ω
$I_{DD}; I_{RD}$	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 100	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/ μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 125	A/ μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/ μs
t_q	$T_{vj} = 125$ °C	100 ... 250	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	250 / 500	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33 \Omega$; typ. / max.	500 / 2000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 250	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; DSC	0,021	K/W
$R_{th(j-c)}$	sin. 180; DSC / SSC	0,0225 / 0,054	K/W
$R_{th(j-c)}$	rec. 120; DSC / SSC	0,027 / 0,06	K/W
$R_{th(c-s)}$	DSC / SSC	0,005 / 0,01	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 130	°C
V_{isol}		-	V~
F	mounting force (SI units)	22 ... 25	kN
	mounting force (US units)	5000 ... 5600	lbf
a			m/s ²
m	approx.	440	g
Case			



SKT

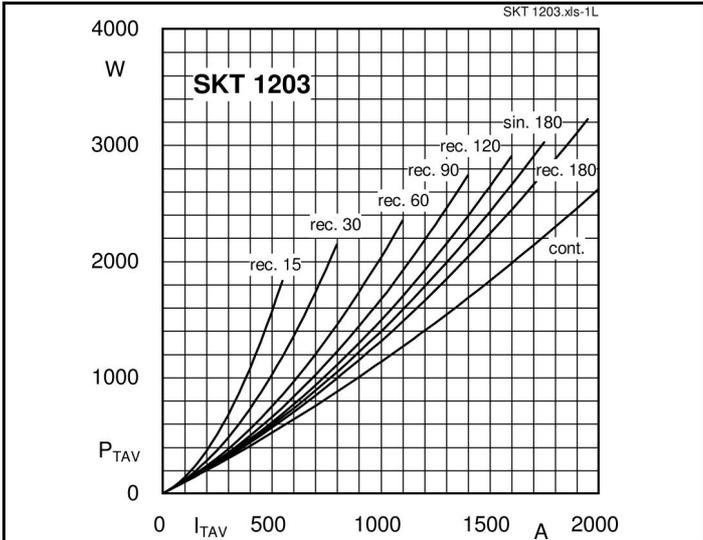


Fig. 1L Power dissipation vs. on-state current

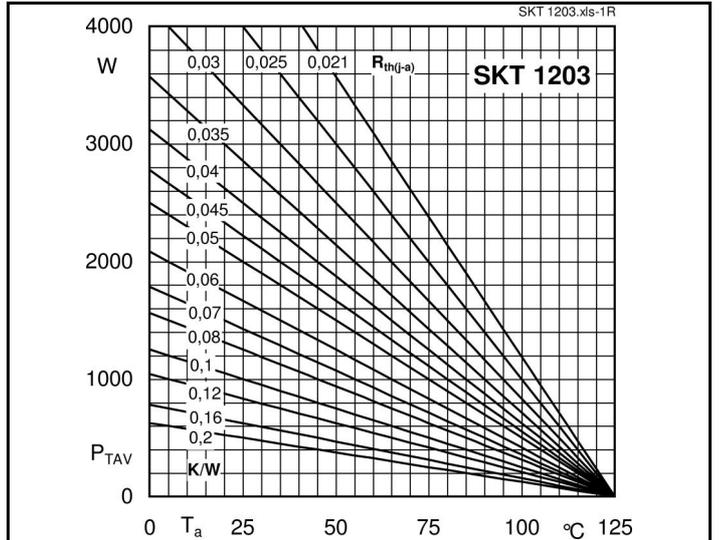


Fig. 1R Power dissipation vs. ambient temperature

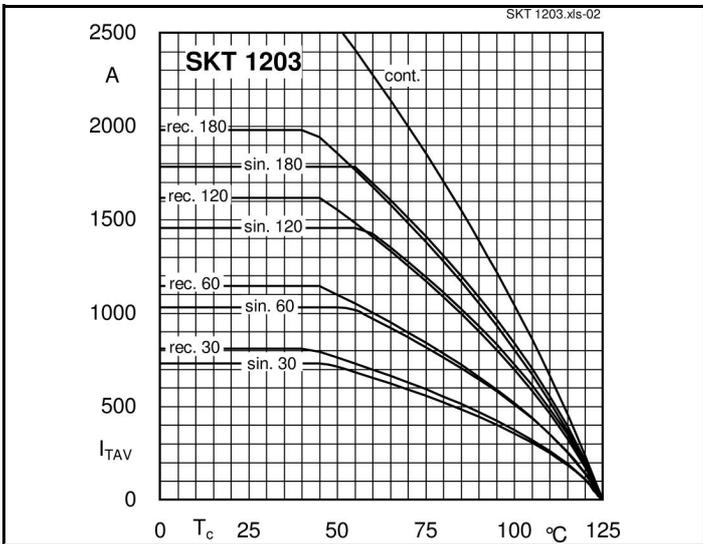


Fig. 2L Rated on-state current vs. case temperature

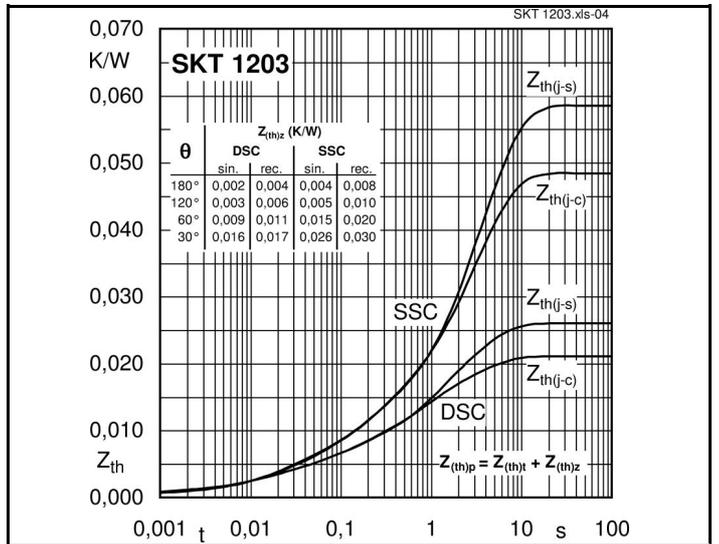


Fig. 4 Transient thermal impedance vs. time

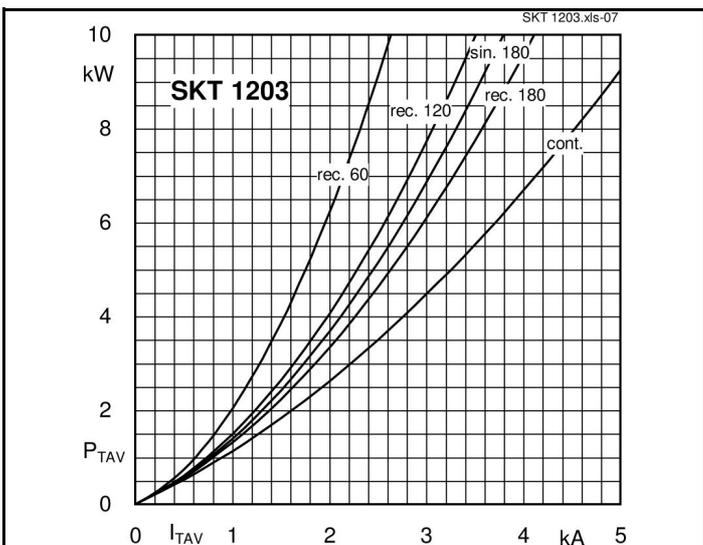


Fig. 7 Power dissipation vs. on-state current

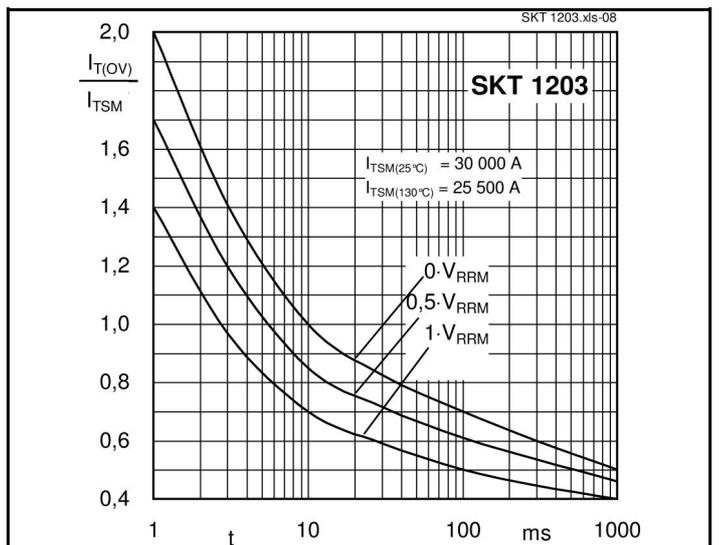
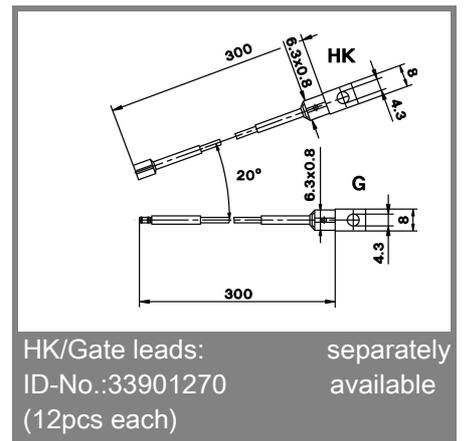
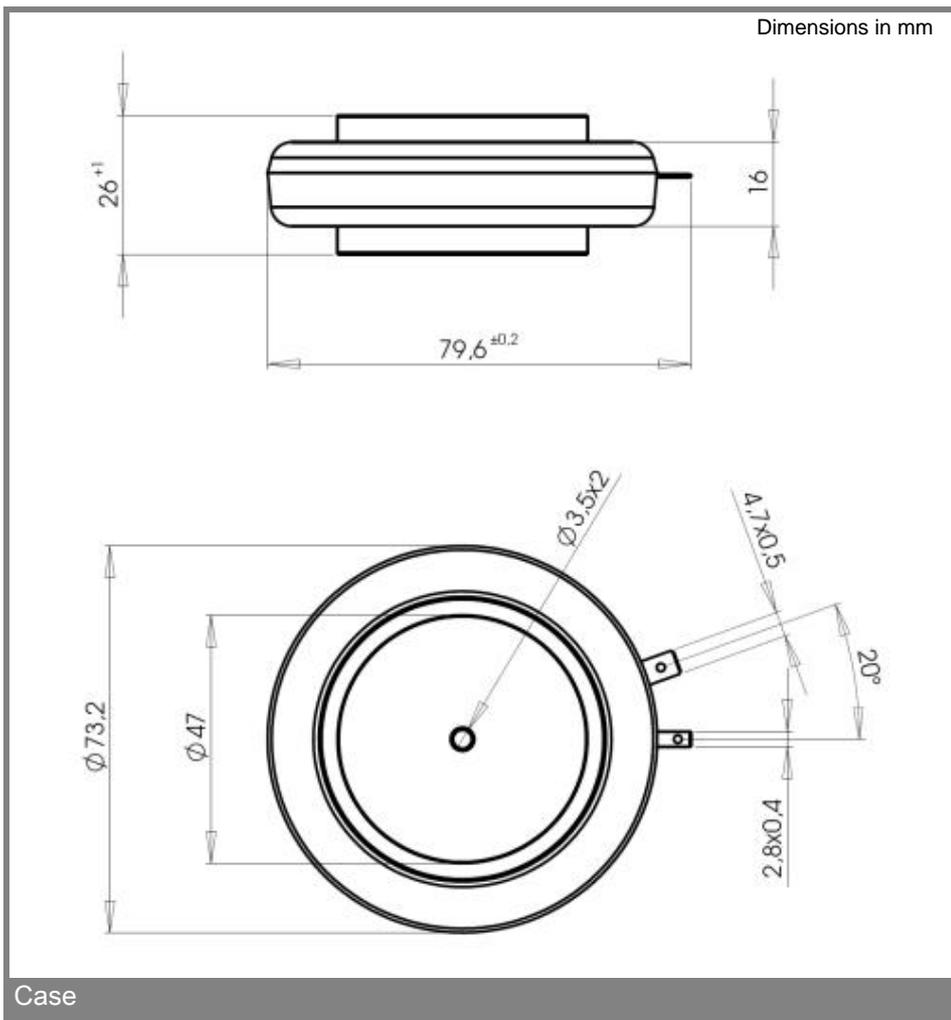


Fig. 8 Surge overload current vs. time



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